NSN 5961-00-836-0609 Thyristor Semiconductor Device - Page 1 of 1



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Inclosure Material:
Metal
Overall Length:
Between 0.330 inches and 0.505 inches
Mounting Facility Quantity:
1
Electrode Internally-electrically Connected To Case:
Anode
Mounting Method:
Threaded stud
Overall Width Across Flats:
Between 0.544 inches and 0.562 inches
Thread Size:
0.250 inches
Semiconductor Material:
Silicon
Voltage Rating In Volts Per Characteristic:
600.0 breakover voltage, dc
Current Rating Per Characteristic:
325.00 amperes forward current, average absolute
Power Rating Per Characteristic:
12.0 watts small-signal input power, common-collector blank
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius case
Thread Series Designator:
Unf
Terminal Type And Quantity:
2 tab, solder lug and 1 threaded stud
Shelf Life:
N/a
Unit Of Measure:
Demilitarization:
No
Fiig:
A110a0